DSA4002

Silicon PNP epitaxial planar type

For general amplification Complementary to DSC4002 DSA2002 in NS through hole type package

Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- \bullet Low collector-emitter saturation voltage $V_{CE(\text{sat})}$
- Contributes to miniaturization of sets, mount area reduction
- Eco-friendly Halogen-free package

Packaging

DSA4002×0A Radial type : 5000 pcs / carton

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol Rating		Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Emitter-base voltage (Collector open)	V _{EBO}	-5	v	
Collector current	I _C	-500	mA	
Peak collector current	I _{CP}	-1	Α	
Collector power dissipation	P _C	300	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Package

- Code
- NS-B2-B

Pin Name

- 1. Emitter
- 2. Collector
- 3. Base

Marking Symbol: A2

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu \text{A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = -10 \mu {\rm A}, I_{\rm C} = 0$	-5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Forward current transfer ratio *1	h _{FE1} *2	$V_{CE} = -10 \text{ V}, I_C = -150 \text{ mA}$	120		340	
	h _{FE2}	$V_{CE} = -10 \text{ V}, I_C = -500 \text{ mA}$	40			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_{\rm C} = -300 \text{ mA}, I_{\rm B} = -30 \text{ mA}$		- 0.2	-0.6	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_{\rm C} = -300 \text{ mA}, I_{\rm B} = -30 \text{ mA}$		- 0.9	- 1.5	V
Transition frequency	f _T	$V_{CE} = -10 \text{ V}, I_C = -50 \text{ mA}$		130		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		7.3	15	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

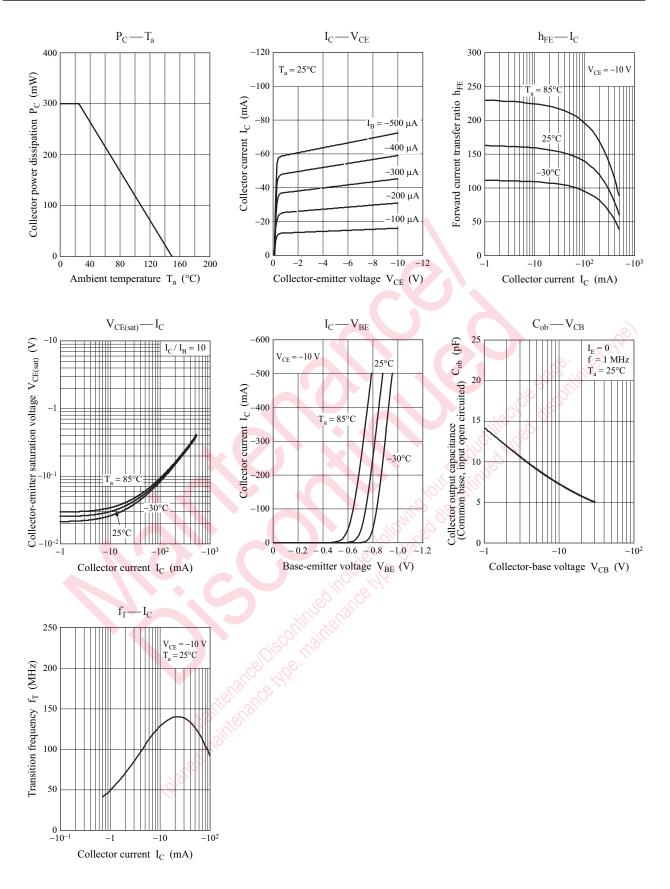
*2: Rank classification

Code	R	S	0
Rank	R	S	No-rank
$h_{\rm FE1}$	120 to 240	170 to 340	120 to 340
Marking Symbol	A2R	A2S	A2

Product of no-rank is not classified and have no marking symbol for rank.

DSA4002

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